

In the Specification:

Please replace paragraph on page 9, line 6, with the following rewritten paragraph:

-- Micro-BGAs 24 have been formed joined to the array of conductive UTSW BLM metal via pads 22 extending from the top surface 6 through to the thinned reverse surface 27 of the UTSW 100. Above each UTSW BLM metal via pads 22 is a metal capture pad 11, each of which served as an etch stop when the holes in which the UTSW BLM metal via pads 22 are located were being formed. The upper surface of the UTSW 100 and the upper surfaces of the metal capture pads 11 are covered with a standard silicon BEOL structure 12. C4 contact pads 13 are formed arrayed on the top surface of the BEOL structure 12 to which chips 44 with C4 solder balls 42 are joined. The C4 solder balls 42 support semiconductor chips 44 on the array of C4 contact pads 42. --

Please replace paragraph on page 12, line 3, with the following rewritten paragraph:

-- It is noted at this point, that by thinning the silicon wafer 10, skipping for a moment to allude briefly to FIG. 2H (which is described in more detail below), a reasonable diameter BLM metal via pads 22 can be created with conventional etching techniques without weakening the UTSW 100 excessively. While it would seem that making the wafer 10 thinner would make it weaker, in fact without thinning, a very large diameter via would be needed requiring a larger plug, thus making the structure weaker because of the Thermal Coefficient of Expansion (TCE) forces exerted by such a large plug which would expand more than a smaller plug. --